Supporting Information for

Hydrogenated under-stoichiometric tungsten oxide anode interlayers for efficient and stable organic photovoltaics

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**Figure S1.** (a) Illustration of the hydrogenation and oxygen vacancies formation mechanisms: The deposition of tungsten oxides by heating a W wire in O\textsubscript{2} environment resulted in the formation of stoichiometric WO\textsubscript{3}. When deposited in reducing environment (i.e. containing hydrogen), the obtained materials are under-stoichiometric. In particular, when deposited in nitrogen environment containing a small amount of atomic hydrogen, an oxygen-deficient tungsten oxide (WO\textsubscript{3-x}) is obtained. In this material oxygen vacancies are generated because of the lack of oxygen in the deposition environment. Through heating the W wire in H\textsubscript{2} environment, hydrogen atoms generated through dissociation of H\textsubscript{2} molecules in the vicinity of the hot-filament are inserted within the WO\textsubscript{3} lattice and are chemically bonded with the lattice (terminal) oxygens. The material obtained in this case is the hydrogenated (hydrogen-doped) H\textsubscript{2}WO\textsubscript{3-x}.
**Figure S2.** Schematic representation of the band structure of WO₃ according to Goodenough’s model for Re₂O₅. In a discrete WO₆ unit the W 5d orbitals with e\(_g\) symmetry overlap with six sp hybrid orbitals of the oxygen atom to give a set of six bonding σ and six antibonding σ* molecular orbitals. In the extended lattice, the discrete energy levels arising from this unit structure will broaden into bands. The W 5d orbitals with the lower t\(_{2g}\) symmetry can overlap with three of the surrounding oxygen p\(_π\) orbitals per octahedron to form bonding π and antibonding π* bands. The π and σ bands are filled and constitute the valence band separated by a large gap (3.15 eV in our case, Figure S3) from the conduction band constituted of π* and σ* bands. The conduction band is empty in WO₃, so this material is a wide bandgap semiconductor, practically an insulator.
Figure S3. Tauc plot derived from absorption measurements for a 10 nm thick WO₃ film: Stoichiometric WO₃ films that were deposited in O₂ environment exhibit an optical bandgap of approximately 3.15 eV, as calculated from the Tauc plot derived from UV-vis absorption spectroscopy measurements (i.e., the intercept of the tangent in the plot of $(\alpha h\nu)^2$ versus $h\nu$ - $\alpha$ is the absorption coefficient - with the $h\nu$ axis gives the bandgap energy).
**Figure S4:** UPS spectra of P3HT:PC$_{71}$BM film (1:0.8% w/w) with a thickness of ca. 20 nm: a HOMO value of 0.9 eV and a $W_F$ of about 4.4 eV can be extracted from these measurements for the P3HT component, resulting in an ionization energy, IE=5.3 eV, in accordance with the literature.$^5$
**Figure S5**: UPS spectra of PCDTBT:PC$_{71}$BM film (1:4 % w/w) with a thickness of *ca.* 20 nm: a HOMO value of 0.5 eV and a $W_F$ of about 4.5 eV can be extracted from these measurements for the PCDTBT component, resulting in an IE=4.95 eV, in accordance with the literature.$^6$
**Figure S6** The variation of $J_{sc}$ (vertical bar) as a function of both active layer and tungsten oxide layers’ thickness (contour plots): we performed optical measurements (we measured the real and imaginary part of the refractive indices) and carried out simulations to calculate the distribution of the overall photocurrent with the variation of the thicknesses of both the active layer and the tungsten oxide films. The short-circuit photocurrent density of each OPV device under normal light incidence can be calculated by using a transmission line model.\(^7\) In ref. 7 the model has been proposed and used for the evaluation of the WO$_3$ thin layer, acting as a spacer between the photoactive layer and the aluminium electrode. Herein, the tungsten oxide has been placed between the ITO and the photoactive layer, acting as a hole collector layer. From the obtained data it can be clearly seen that optical effects are not very significant in our devices, where the active layer’s thickness is nearly 100 nm and the tungsten oxide layer is about 10 nm. As a matter of fact, both under-stoichiometric tungsten oxides, and especially the hydrogen-doped one, are probably inferior optical spacers than the stoichiometric one.
References


